



## 2.0-8.0GHz, 10W, 28V GaN Fully matched PA Module

The XMAH2080-10C9 is a 10-watt, single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from 2 to 8GHz. The module is  $50\ \Omega$  input/output matched and requires minimal external components. **Within 4 to 8GHz, it can deliver more than 12W.** The module implements wideband power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.



$V_{ds} = 28V, V_{gs} = -2.37V, I_{dq} = 25mA$ CW					
Freq(MHz)	P-1(dBm)	P-1Gain(dB)	P-3(dBm)	P-3W	EFF (%)
2000	38.16	10.6	40.12	10.3	38.2
2200	39.25	11.8	40.81	12.1	46.2
2400	39.58	12.0	41.11	12.9	49.3
2600	39.65	12.1	41.48	14.1	50.6
2800	39.61	11.8	41.44	13.9	49.7
3000	38.88	11.6	40.92	12.4	45.2
3200	39.61	12.6	41.16	13.1	53.8
3400	39.70	12.6	41.23	13.3	55.3
3600	39.31	12.3	41.13	13.0	50.3
3800	39.12	11.9	41.03	12.7	46.4
4000	39.01	11.6	41.33	13.6	43.1
4200	39.08	12.1	41.27	13.4	43.8
4400	39.37	12.0	41.58	14.4	45.8
4600	39.29	12.1	41.69	14.8	44.7
4800	39.02	12.9	41.66	14.7	45.5
5000	39.31	13.3	41.95	15.7	49.5
5200	39.43	13.1	41.93	15.6	50.1
5400	39.11	12.3	41.62	14.5	47.1
5600	39.12	12.4	41.53	14.2	46.0
5800	39.59	12.1	41.77	15.0	50.2
6000	39.96	11.7	41.90	15.5	56.4
6200	40.19	12.0	41.99	15.8	63.5
6400	39.78	11.5	41.65	14.6	60.0
6600	39.60	11.1	41.55	14.3	56.7
6800	39.35	10.1	41.17	13.1	53.3
7000	39.41	9.8	41.24	13.3	53.7
7200	39.23	10.3	41.15	13.0	51.1
7400	39.30	11.0	41.37	13.7	52.0
7600	39.26	10.7	41.30	13.5	50.8
7800	39.26	10.4	41.25	13.3	52.3
8000	39.34	10.3	41.31	13.5	53.6



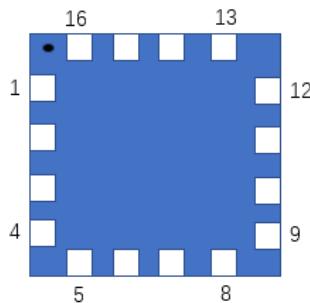
## Product Features

- Operating Frequency Range: 2-8GHz
- Operating Drain Voltage: +28 V (Up to 32V)
- 50 Ω Input/Output
- Psat $\geq$ 40 dBm
- Power gain: $>8$ dB
- Minimum efficiency: $>35$ %
- 12x10 mm Surface Mount Package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

## Applications

- Ultra Broadband Amplifiers
- Fiber Drivers
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

## Pin Configuration and Description (Top view)



Pin No.	Symbol	Description
4	RF IN	RF Input
9	RF OUT	RF Output
6	V <sub>gs</sub>	Gate bias
7	V <sub>dd</sub>	Drain bias
Others	NC	No connection
Package Base	GND	DC/RF Ground. Proposed to be soldered to heatsink plane directly for the best CW thermal and RF performance. Soldered through high density vias or copper coin also allowed ,but will result in excessive junction temperatures and different RF performance

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V <sub>DSS</sub>	150	Vdc
Gate--Source Voltage	V <sub>GS</sub>	-10 to +2	Vdc
Operating Voltage	V <sub>DD</sub>	+36	Vdc
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C
Case Operating Temperature	T <sub>C</sub>	+150	°C
Operating Junction Temperature	T <sub>J</sub>	+225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_c = 85^\circ\text{C}$ , DC test	$R_{\theta JC}$	6	$^\circ\text{C/W}$

**Table 3. Electrical Characteristics**

Parameter	Condition	Min	Typ	Max	Unit
Frequency Range		2000		8000	MHz
Power Gain @ $P_{\text{sat}}$		8			dB
$P_{\text{SAT}}$	Pulse	40	41		dBm
Drain Efficiency @ $P_{\text{SAT}}$		35			%

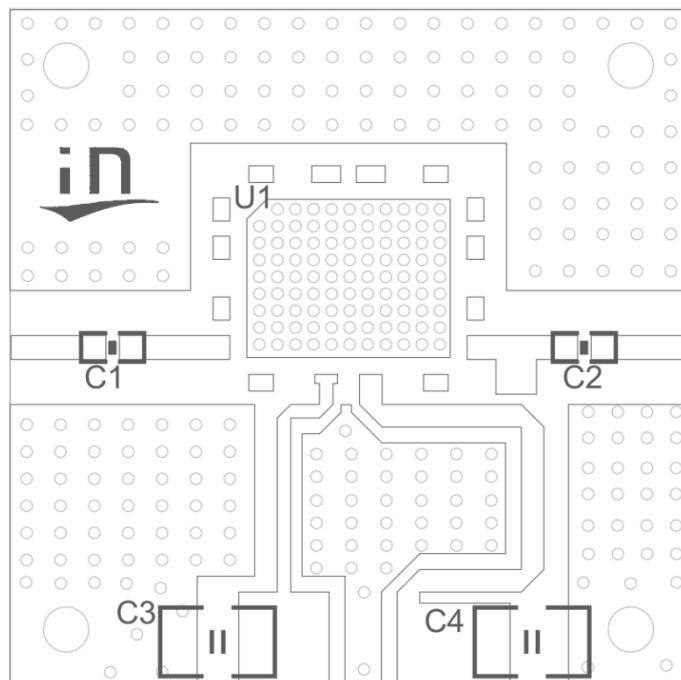
Unless otherwise noted:  $TA = 25^\circ\text{C}$ ,  $V_{DD} = 28$  V, Pulse Width=50 us, Duty cycle=20%

**Load Mismatch of per Section (On Test Fixture, 50 ohm system):**  $V_{DD}=28$  V,  $I_{DQ}=25$  mA,  $f=6$  GHz

VSWR 10:1 at $P_{\text{sat}}$ pulse CW Output Power	No Device Degradation
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## Reference Circuit of Test Fixture Assembly Diagram

Figure 1. Test Circuit Component Layout



Component	Value	Description
U1	XMAH2080-10C9	PA (12.2*10.2mm)
C1、C2	3.9pF	0603
C3、C4	10uF	1206

## TYPICAL CHARACTERISTICS

Figure 2. Network analyzer output S11/S21 (Pin=0dBm)

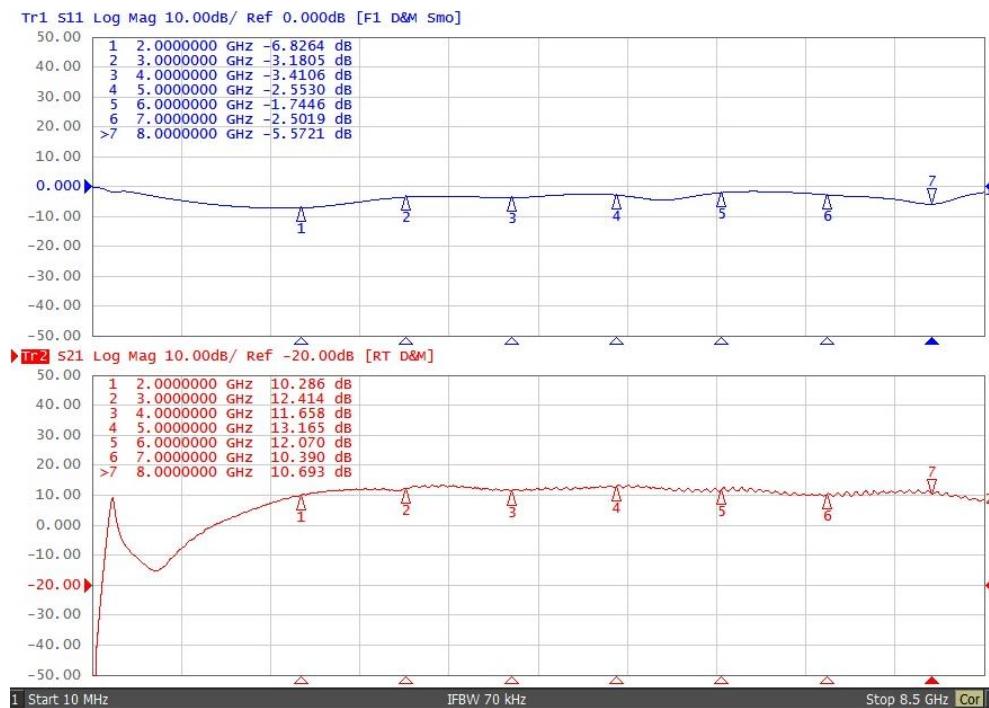
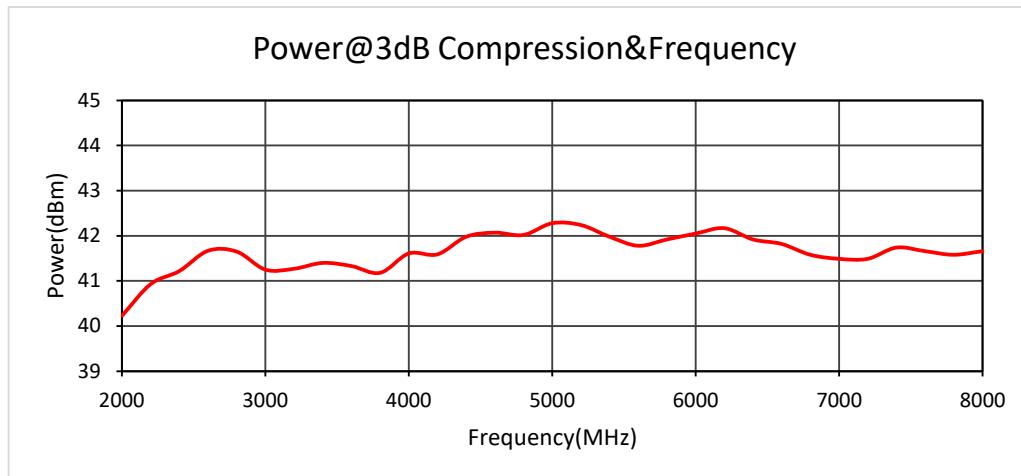
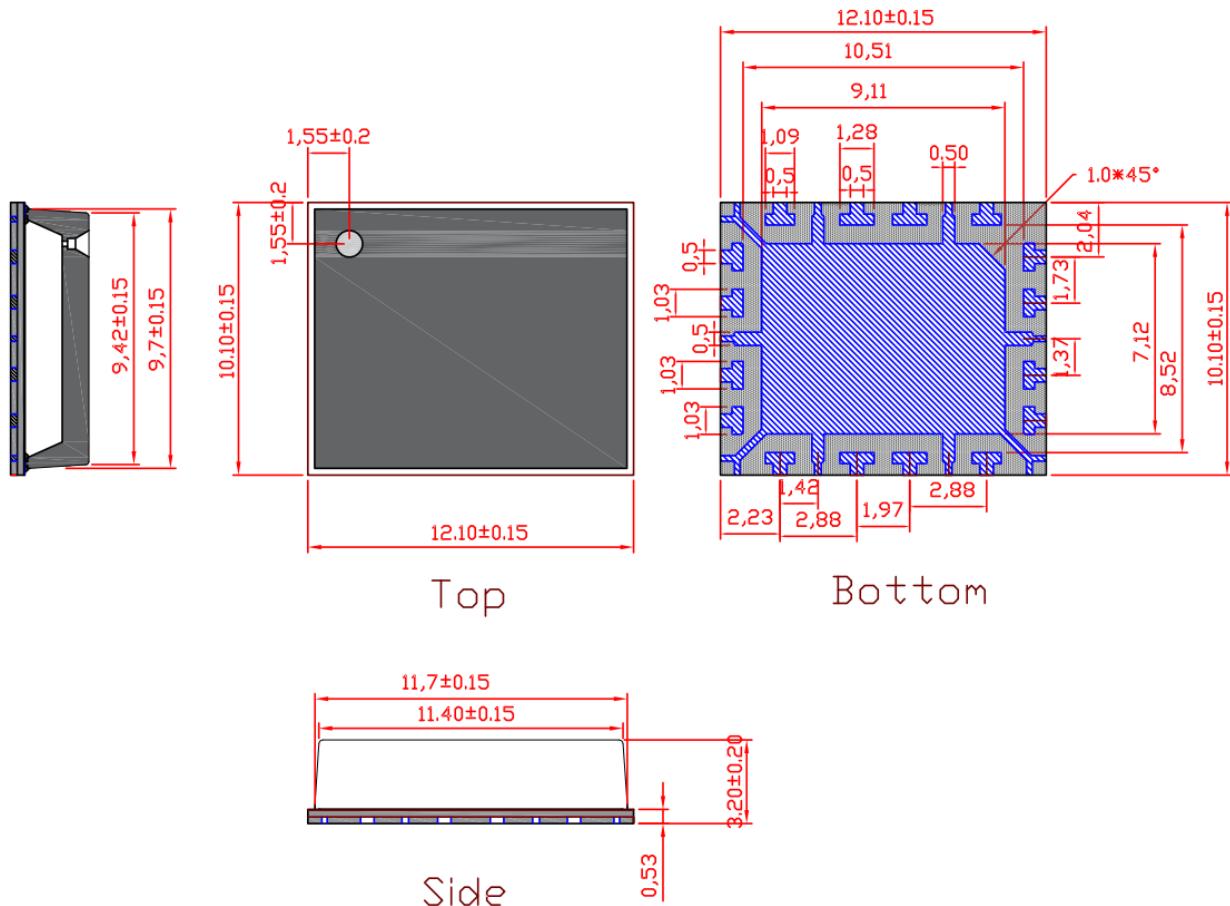


Figure 3. P3dB across the band at 28V



## Package Dimensions (Unit:mm)



## Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2025/12/19	Rev 1.0	Preliminary Datasheet

Application data based on HJ-25-23

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